

PCN Number:		20240116003.1		PCN Date:		January 16, 2024																			
Title:		Qualification of RFAB using qualified Process Technology and Die Revision for select devices																							
Customer Contact:		Change Management Team		Dept:		Quality Services																			
Proposed 1st Ship Date:		Apr 16, 2024		Sample requests accepted until:		Feb 16, 2024*																			
*Sample requests received after February 16, 2024 will not be supported.																									
Change Type:																									
<input type="checkbox"/>	Assembly Site	<input checked="" type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Material																				
<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet	<input type="checkbox"/>	Wafer Bump Process																				
<input type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input checked="" type="checkbox"/>	Wafer Fab Site																				
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site	<input checked="" type="checkbox"/>	Wafer Fab Material																				
<input checked="" type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input checked="" type="checkbox"/>	Wafer Fab Process																				
PCN Details																									
Description of Change:																									
Texas Instruments is pleased to announce the addition of RFAB using the TIB qualified process technology for select devices listed below in the product affected section.																									
<table><tr><th colspan="3">Current Fab Site</th><th colspan="3">Additional Fab Site</th></tr><tr><th>Current Fab Site</th><th>Process</th><th>Wafer Diameter</th><th>Additional Fab Site</th><th>Process</th><th>Wafer Diameter</th></tr><tr><td>SFAB</td><td>J11</td><td>150 mm</td><td>RFAB</td><td>TIB</td><td>300 mm</td></tr></table>						Current Fab Site			Additional Fab Site			Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	SFAB	J11	150 mm	RFAB	TIB	300 mm		
Current Fab Site			Additional Fab Site																						
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter																				
SFAB	J11	150 mm	RFAB	TIB	300 mm																				
The die was also changed as a result of the process change.																									
Qual details are provided in the Qual Data Section.																									
Reason for Change:																									
These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.																									
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																									
None																									
Changes to product identification resulting from this PCN:																									
Fab Site Information:																									
<table><tr><td>Chip Site</td><td>Chip Site Origin Code (20L)</td><td>Chip Site Country Code (21L)</td><td>Chip Site City</td></tr><tr><td>SH-BIP-1</td><td>SHE</td><td>USA</td><td>Sherman</td></tr><tr><td>RFAB</td><td>RFB</td><td>USA</td><td>Richardson</td></tr></table>				Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City	SH-BIP-1	SHE	USA	Sherman	RFAB	RFB	USA	Richardson										
Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City																						
SH-BIP-1	SHE	USA	Sherman																						
RFAB	RFB	USA	Richardson																						
Die Rev:																									
<table><tr><td>Current</td><td>New</td></tr><tr><td>Die Rev [2P]</td><td>Die Rev [2P]</td></tr><tr><td>F</td><td>A</td></tr></table>				Current	New	Die Rev [2P]	Die Rev [2P]	F	A																
Current	New																								
Die Rev [2P]	Die Rev [2P]																								
F	A																								

Sample product shipping label (not actual product label)



**TEXAS
INSTRUMENTS**
MADE IN: Malaysia
2DC: 2Q:

MSL '2 /260C/1 YEAR	SEAL DT
MSL 1 /235C/UNLIM	03/29/04

OPT:
ITEM: 39
LBL: 5A (L)T0:1750





(1P) SN74LS07NSR
(Q) 2000 (D) 0336
(31T) LOT: 3959047MLA
(4W) TKY (1T) 7523483SI2
(P)
(2P) REV: (V) 0033317
(20L) CS0: SHE (21L) CC0:USA
(22L) AS0: MLA (23L) ACO: MYS

Product Affected:

ULN2003ADR

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Name	Condition	Duration	Qual Device: ULN2003ADR	QBS Reference: MC33063ADR	QBS Reference: MC33063AQDRQ1	QBS Reference: ULN2003ADR
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	-	-
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	3/231/0	-	-
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	3/231/0	-	-
HTSL	A6	High Temperature Storage Life	170C	420 Hours	-	3/231/0	-	-
HTOL	B1	Life Test	125C	1000 Hours	-	2/154/0	3/231/0	-
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	1/800/0	3/2400/0	-

Type	#	Test Name	Condition	Duration	Qual Device: ULN2003ADR	QBS Reference: MC33063ADR	QBS Reference: MC33063AQDRQ1	QBS Reference: ULN2003ADR
ESD	E2	ESD CDM	-	250 Volts	-	-	-	1/3/0
ESD	E2	ESD HBM	-	1000 Volts	-	-	-	1/3/0
LU	E4	Latch-Up	Per JESD78	-	-	-	-	1/3/0
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	-	-	1/30/0

- QBS: Qual By Similarity
- Qual Device ULN2003ADR is qualified at MSL1 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2209-040

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Name	Condition	Duration	Qual Device: ULN2003ADR	QBS Reference: MC33063ADR	QBS Reference: MC33063ADR	QBS Reference: MC33063AQDRQ1
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	-	3/231/0	3/231/0
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	-	3/231/0	3/231/0
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	-	3/231/0	3/231/0
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	-	-	-	3/135/0
HTSL	A6	High Temperature Storage Life	170C	420 Hours	-	-	3/231/0	-

Type	#	Test Name	Condition	Duration	Qual Device: ULN2003ADR	QBS Reference: MC33063ADR	QBS Reference: MC33063ADR	QBS Reference: MC33063AQDRQ1
HTOL	B1	Life Test	125C	1000 Hours	-	2/154/0	1/77/0	3/231/0
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	1/800/0	2/1600/0	3/2400/0
SD	C3	PB Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	-	-	-	-	1/15/0
SD	C3	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	-	-	-	-	1/15/0
PD	C4	Physical Dimensions	Cpk>1.67	-	-	-	-	3/30/0
ESD	E2	ESD CDM	-	250 Volts	1/3/0	-	-	-
ESD	E2	ESD HBM	-	1000 Volts	1/3/0	-	-	-
LU	E4	Latch-Up	Per JESD78	-	1/3/0	-	-	-
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	-	-	-

- QBS: Qual By Similarity
- Qual Device ULN2003ADR is qualified at MSL1 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
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Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2209-042

For questions regarding this notice, e-mails can be sent to Change Management team or your local Field Sales Representative.

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